

Excellent Integrated System Limited

Stocking Distributor

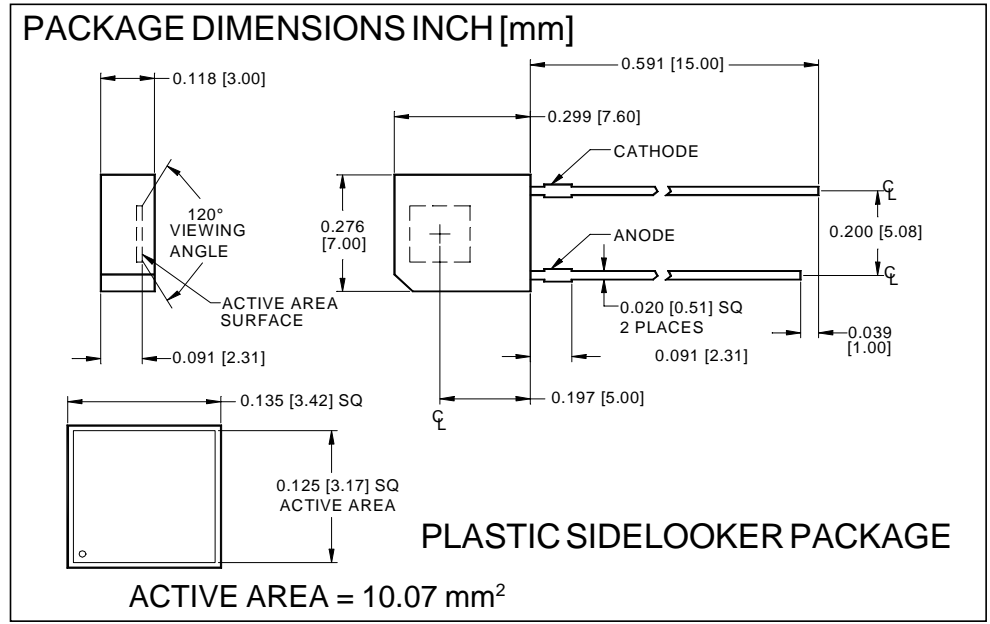
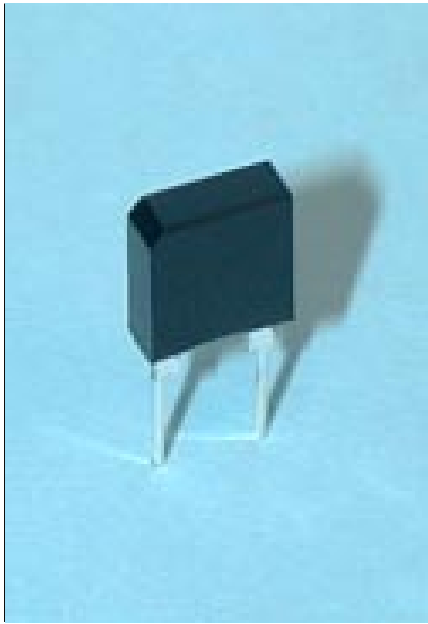
Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Advanced Photonix, Inc.](#)
[PDB-C159](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

Silicon Photodiode, Blue Enhanced Photoconductive
with daylight filter Type PDB-C159F



FEATURES

- Large active area
- High speed
- Low cost

DESCRIPTION: The **PDB-C159F** detector is a 9.00 mm² planar pin photodiode packaged in a black plastic side-looker housing. Designed for high speed, low capacitance, photoconductive applications. The **PDB-C159F** includes a daylight filter.

APPLICATIONS

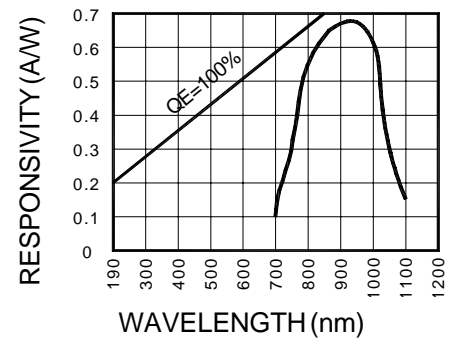
- I.R. links
- I.R. sensors
- I.R. remotes

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-30	+100	°C
T _O	Operating Temperature Range	-25	+85	°C
T _S	Soldering Temperature*		+240	°C
I _L	Light Current		500	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	59	68		μA
I _D	Dark Current	H = 0, V _R = 10 V		5	30	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	75	100		MΩ
TCR _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 10 V*		15	20	pF
λrange	Spectral Application Range	(with daylight filter)	700		1100	nm
λp	Spectral Response - Peak			950		nm
V _{BR}	Breakdown Voltage	I = 10 μA	25	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		7x10 ⁻¹³		W/√Hz
tr	Response Time	RL = 1 KΩ V _R = 10 V		50		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. *f = 1 MHz, [FORM NO. 100-PDB-C159 REV A]